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AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

Claims 1-7 (canceled).

Claim 8 (currently amended): The duplexer according to Claim 6, wherein A duplexer, comprising:

a transmission-side band filter including a plurality of surface acoustic wave resonators connected together to define a ladder circuit;

a reception-side band filter including a plurality of surface acoustic wave resonators connected together to define a ladder circuit; wherein

each of the plurality of surface acoustic wave resonators of the transmission-side band filter and the reception-side band filter includes a 47° to 58° rotated, Y-cut, X-propagating LiNbO₃ substrate and an IDT electrode provided on the LiNbO₃ substrate;

the IDT electrode includes a Ti foundation electrode layer disposed on the LiNbO₃ substrate and an Al electrode layer disposed on the Ti foundation electrode layer; and

a (111) face of the Al electrode layer, one of a (001) face and (100) face of the Ti foundation electrode layer, and a (001) face of the LiNbO₃ substrate are aligned in parallel;

where the Ti foundation electrode layer is an epitaxially grown electrode layer on the LiNbO₃ substrate and the Al electrode layer is an epitaxially grown electrode layer on the Ti foundation electrode layer;

in the reception-side band filter, a first inductance is disposed in parallel with respect to at least one serial arm resonator connected to a serial arm of the ladder circuit among the plurality of surface acoustic wave resonators, and in the transmission-

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side band filter, a second inductance is disposed between a parallel arm resonator connected to a parallel arm of the ladder circuit among the plurality of surface acoustic wave resonators and a ground potential; and

the second inductance is defined by a line embedded in the duplexer.

Claim 9 (currently amended): The duplexer according to Claim 8, wherein the first inductance and the second inductance are respectively is defined by at least one of a wire bonding used for electrical connection in the duplexer, a line embedded in the duplexer, and an external coil component.

Claim 10 (canceled).

Claim 11 (currently amended): The duplexer according to Claim 68, wherein the transmission-side band filter includes three serial arm resonators and two parallel arm resonators defining the ladder circuit.

Claim 12 (currently amended): The duplexer according to Claim 68, wherein the reception-side band filter includes three serial arm resonators and two parallel arm resonators defining the ladder circuit.

Claim 13 (currently amended): The duplexer according to Claim 68, wherein the LiNbO₃ substrate is a 55° rotated, Y-cut, X-propagating LiNbO₃ substrate.

Claim 14 (currently amended): A communication device, comprising the duplexer according to Claim 68, wherein the duplexer includes an antenna terminal, an inductance is disposed between the antennal terminal and an antenna, and the duplexer further includes a capacitor connected between a connection point between the inductance and the antenna and a ground potential.

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Claims 15-24 (canceled).

Claim 25 (new): The duplexer according to Claim 8, wherein the transmission-side band filter and the reception-side band filter are mounted by a flip chip bonding method.